







P1086, P1087 P-Channel JFET

Features

- InterFET P0099F Geometry
- Low Noise: 8 nV/VHz Typical
- Low Rds(on): 75 Ohms Maximum (P1086)
- RoHS Compliant
- SMT, TH, and Bare Die Package options.

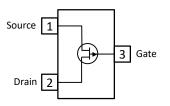
Applications

- Choppers
- Analog Switches

Description

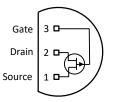
The 30V InterFET P1086 and P1087 JFET's are targeted for low noise switching and chopper applications.

SOT23 Top View





TO-92 Bottom View





Product Summary

Parameters		P1086 Min	P1087 Min	Unit
BV _{GSS}	Gate to Source Breakdown Voltage	30	30	V
I _{DSS}	Drain to Source Saturation Current	-10	-5	mA
V _{GS(off)}	Gate to Source Cutoff Voltage	10 (max)	5 (max)	V

Ordering Information Custom Part and Binning Options Available

Part Number	Description	Case	Packaging
P1086; P1087	Through-Hole	TO-92	Bulk
SMPP1086; SMPP1087	Surface Mount	SOT23	Bulk
	7" Tape and Reel: Max 3,000 Pieces		Minimum 1,000 Pieces
SMPP1086TR; SMPP1087TR	13" Tape and Reel: Max 9,000 Pieces	SOT23	Tape and Reel
P1086COT; P1087COT	Chip Orientated Tray (COT Waffle Pack)	COT	400/Waffle Pack
P1086CFT; P1087CFT	Chip Face-up Tray (CFT Waffle Pack)	CFT	400/Waffle Pack



Disclaimer: It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.









Electrical Characteristics

Maximum Ratings (@ T_A = 25°C, Unless otherwise specified)

	Parameters	Value	Unit
V_{RGS}	Reverse Gate Source and Gate Drain Voltage	30	V
I _{FG}	Continuous Forward Gate Current	50	mA
PD	Continuous Device Power Dissipation	360	mW
Р	Power Derating	3.27	mW/°C
Τı	Operating Junction Temperature	-55 to 125	°C
T _{STG}	Storage Temperature	-65 to 200	°C

Static Characteristics (@ TA = 25°C, Unless otherwise specified)

			P1	086 P1		087	
	Parameters	Conditions	Min	Max	Min	Max	Unit
V _{(BR)GSS}	Gate to Source Breakdown Voltage	$V_{DS} = 0V$, $I_G = 1\mu A$	30		30		V
I _{GSS}	Gate to Source Reverse Current	V_{GS} = 15V, V_{DS} = 0V		2		2	nA
V _{GS(OFF)}	Gate to Source Cutoff Voltage	$V_{DS} = -15V$, $I_D = -1\mu A$		10		5	V
I _{DSS}	Drain to Source Saturation Current	$V_{GS} = 0V$, $V_{DS} = -20V$ (Pulsed)	-10		-5		mA
I _{D(OFF)}	Drain Cutoff Current	$V_{DS} = -15V, \\ P1086: V_{GS} = 12V \\ P1087: V_{GS} = 7V \\ T_A = 25^{\circ}C \\ T_A = 85^{\circ}C$		-10 -0.5		-10 -0.5	nA μA
I _{DGO}	Drain Reverse Current	$V_{DG} = -15V$, $I_S = 0A$, $T_A = 25$ °C $V_{DG} = -15V$, $I_S = 0A$, $T_A = 85$ °C		2 0.1		2 0.1	nA μA
V _{DS(ON)}	Drain to Source ON Voltage	P1086: $V_{GS} = 0V$, $I_D = -6mA$ P1087: $V_{GS} = 0V$, $I_D = -3mA$		-0.5 -0.5		-0.5 -0.5	V
R _{DS(ON)}	Static Drain to Source ON Resistance	I _D = -1mA, V _{GS} = 0V		75		150	Ω

Dynamic Characteristics (@ TA = 25°C, Unless otherwise specified)

_			P1086		P1087		
	Parameters	Conditions	Min	Max	Min	Max	Unit
R _{DS(ON)}	Drain to Source ON Resistance	$I_D = 0A$, $V_{GS} = 0V$, $f = 1kHz$		75		150	Ω
Ciss	Input Capacitance	V _{DS} = -15V, V _{GS} = 0V, f = 1kHz		45		45	pF
_	Reverse Transfer	P1086: V _{DS} = 0V, V _{GS} = 12V, f = 1MHz		10		10	nΕ
C _{rss}	Capacitance	P1087: V _{DS} = 0V, V _{GS} = 7V, f = 1MHz		10		10	pF
t _{d(ON)}	Turn ON Delay Time	V 64.V 94		15		15	ns
tr	Rise Time	V _{DD} = -6V, V _{GS(ON)} = 0V P1086: V _{GS(OFF)} = 12V, I _{D(ON)} = -6mA,		20		20	ns
t _{d(OFF)}	Turn OFF Delay Time	$R_{L}=910\Omega \\ P1087: V_{GS(OFF)}=7V, I_{D(ON)}=-3mA, \\ R_{L}=1.8K\Omega \\ \\ -$		15		25	ns
t _f	Fall Time			50		100	ns



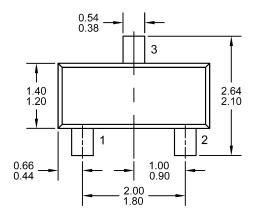


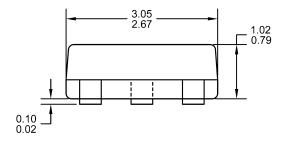




SOT23 (TO-236AB) Mechanical and Layout Data

Package Outline Data





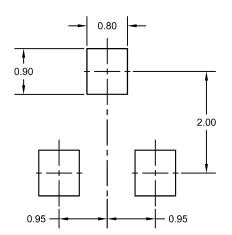
0.61 0.45 0.27 0.13

0.15

0.09

- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.12 grams
- 3. Molded plastic case UL 94V-0 rated
- For Tape and Reel specifications refer to InterFET CTC-021 Tape and Reel Specification, Document number: IF39002
- Bulk product is shipped in standard ESD shipping material
- 6. Refer to JEDEC standards for additional information.

Suggested Pad Layout



- 1. All linear dimensions are in millimeters.
- 2. The suggested land pattern dimensions have been provided for reference only. A more robust pattern may be desired for wave soldering.



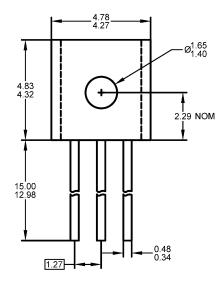


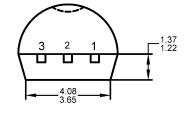


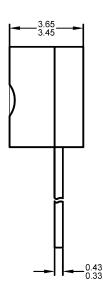


TO-92 Mechanical and Layout Data

Package Outline Data

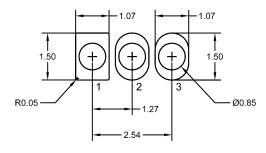






- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.19 grams
- 3. Molded plastic case UL 94V-0 rated
- Bulk product is shipped in standard ESD shipping material
- 5. Refer to JEDEC standards for additional information.

Suggested Through-Hole Layout



- 1. All linear dimensions are in millimeters.
- The suggested land pattern dimensions have been provided as a straight lead reference only. A more robust pattern may be desired for wave soldering and/or bent lead configurations.

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